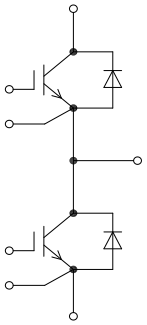
技术信息 / Technical Information

IGBT-模块
IGBT-Module

2A200HB12C2F





V_{CES} = 1200V
$I_{C\ nom}$ = 200A / I_{CRM} = 400A

典型应用
- 电机传动

Typical Applications
- Motor drives

电气特性
- 低开关损耗
- $T_{vj\ op}$ = 150°C

Electrical Features
- Low switching losses
- $T_{vj\ op}$ = 150°C

机械特性
- 铜基板

Mechanical Features
- Copper base plate

Module Label Code

Barcode Code 128

Sample
00000123456000000000000

DMX - Code

Content of the Code	Digit
Module Serial Number	1 - 5
Module Material Number	6 - 11
Production Order Number	12 - 19
Datecode (Production Year)	20 - 21
Datecode (Production Week)	22 - 23

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IGBT, 逆变器 / IGBT,Inverter

最大额定值 / Maximum Rated Values

集电极 - 发射极电压 Collector-emitter voltage	T_{vj} = 25°C	V_{CES}	1200		V
连续集电极直流电流 Continuous DC collector current	T_C = 95°C, $T_{vj\,max}$ = 175°C T_C = 25°C, $T_{vj\,max}$ = 175°C	$I_{C\,nom}$ I_C	200 294		A A
集电极重复峰值电流 Repetitive peak collector current	t_P = 1 ms	I_{CRM}	400		A
总功率损耗 Total power dissipation	T_C = 25°C, $T_{vj\,max}$ = 175°C	P_{tot}	1100		W
栅极 - 发射极峰值电压 Gate-emitter peak voltage		V_{GES}	+/-20		V

特征值 / Characteristic Values

			min.	typ.	max.	
集电极 - 发射极饱和电压 Collector-emitter saturation voltage	I_C = 200 A, V_{GE} = 15 V T_{vj} = 25°C I_C = 200 A, V_{GE} = 15 V T_{vj} = 125°C I_C = 200 A, V_{GE} = 15 V T_{vj} = 150°C	$V_{CE\,sat}$		1,85 2,20 2,30	2,25	V V V
栅极阈值电压 Gate threshold voltage	I_C = 6,60 mA, V_{CE} = V_{GE}, T_{vj} = 25°C	V_{GEth}	5,20	5,80	6,40	V
栅极电荷 Gate charge	V_{GE} = -15 V ... +15 V	Q_G		1,40		µC
内部栅极电阻 Internal gate resistor	T_{vj} = 25°C	R_{Gint}		3,7		Ω
输入电容 Input capacitance	f = 1 MHz, T_{vj} = 25°C, V_{CE} = 25 V, V_{GE} = 0 V	C_{ies}		11,0		nF
反向传输电容 Reverse transfer capacitance	f = 1 MHz, T_{vj} = 25°C, V_{CE} = 25 V, V_{GE} = 0 V	C_{res}		0,47		nF
集电极-发射极截止电流 Collector-emitter cut-off current	V_{CE} = 1200 V, V_{GE} = 0 V, T_{vj} = 25°C	I_{CES}			5,0	mA
栅极-发射极漏电流 Gate-emitter leakage current	V_{CE} = 0 V, V_{GE} = 20 V, T_{vj} = 25°C	I_{GES}			400	nA
开通延迟时间(电感负载) Turn-on delay time, inductive load	I_C = 200 A, V_{CE} = 600 V T_{vj} = 25°C V_{GE} = ±15 V T_{vj} = 125°C R_{Gon} = 0,62 Ω T_{vj} = 150°C	$t_{d\,on}$		0,13 0,13 0,14		µs µs µs
上升时间(电感负载) Rise time, inductive load	I_C = 200 A, V_{CE} = 600 V T_{vj} = 25°C V_{GE} = ±15 V T_{vj} = 125°C R_{Gon} = 0,62 Ω T_{vj} = 150°C	t_r		0,03 0,03 0,04		µs µs µs
关断延迟时间(电感负载) Turn-off delay time, inductive load	I_C = 200 A, V_{CE} = 600 V T_{vj} = 25°C V_{GE} = ±15 V T_{vj} = 125°C R_{Goff} = 0,62 Ω T_{vj} = 150°C	$t_{d\,off}$		0,30 0,38 0,40		µs µs µs
下降时间(电感负载) Fall time, inductive load	I_C = 200 A, V_{CE} = 600 V T_{vj} = 25°C V_{GE} = ±15 V T_{vj} = 125°C R_{Goff} = 0,62 Ω T_{vj} = 150°C	t_f		0,05 0,07 0,08		µs µs µs
开通损耗能量 (每脉冲) Turn-on energy loss per pulse	I_C = 200 A, V_{CE} = 600 V, L_S = 25 nH T_{vj} = 25°C V_{GE} = ±15 V, di/dt = 5400 A/µs (T_{vj} = 150°C) T_{vj} = 125°C R_{Gon} = 0,62 Ω T_{vj} = 150°C	E_{on}		13,5 22,5 25,5		mJ mJ mJ
关断损耗能量 (每脉冲) Turn-off energy loss per pulse	I_C = 200 A, V_{CE} = 600 V, L_S = 25 nH T_{vj} = 25°C V_{GE} = ±15 V, du/dt = 3600 V/µs (T_{vj} = 150°C) T_{vj} = 125°C R_{Goff} = 0,62 Ω T_{vj} = 150°C	E_{off}		12,5 20,0 22,5		mJ mJ mJ
短路数据 SC data	V_{GE} ≤ 15 V, V_{CC} = 800 V V_{CEmax} = V_{CES} -L_{sCE} ·di/dt t_P ≤ 10 µs, T_{vj} = 150°C	I_{SC}		700		A
结 - 外壳热阻 Thermal resistance, junction to case	每个 IGBT / per IGBT	R_{thJC}			0,134	K/W
外壳 - 散热器热阻 Thermal resistance, case to heatsink	每个 IGBT / per IGBT λ_{Paste} = 1 W/(m·K) / λ_{grease} = 1 W/(m·K)	R_{thCH}		0,100		K/W
在开关状态下温度 Temperature under switching conditions		$T_{vj\,op}$	-40		150	°C

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二极管,逆变器 / Diode, Inverter

最大额定值 / Maximum Rated Values

反向重复峰值电压 Repetitive peak reverse voltage	T_{vj} = 25°C	V_{RRM}	1200		V
连续正向直流电流 Continuous DC forward current		I_F	200		A
正向重复峰值电流 Repetitive peak forward current	t_P = 1 ms	I_{FRM}	400		A
I2t-值 I²t - value	V_R = 0 V, t_P = 10 ms, T_{vj} = 125°C V_R = 0 V, t_P = 10 ms, T_{vj} = 150°C	I²t	6400 5850		A²s A²s

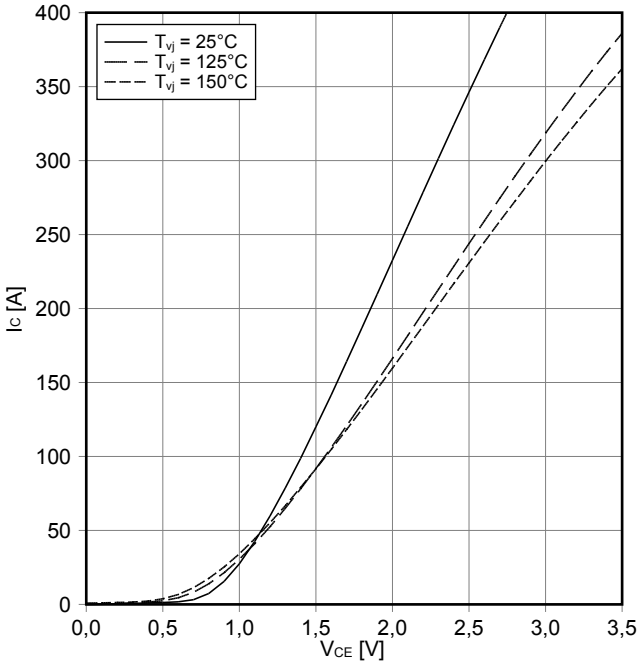
特征值 / Characteristic Values

			min.	typ.	max.	
正向电压 Forward voltage	I_F = 200 A, V_{GE} = 0 V I_F = 200 A, V_{GE} = 0 V I_F = 200 A, V_{GE} = 0 V	T_{vj} = 25°C T_{vj} = 125°C T_{vj} = 150°C	V_F		1,65 1,65 1,65	2,10	V V V
反向恢复峰值电流 Peak reverse recovery current	I_F = 200 A, - di_F/dt = 5400 A/µs (T_{vj}=150°C) V_R = 600 V V_{GE} = -15 V	T_{vj} = 25°C T_{vj} = 125°C T_{vj} = 150°C	I_{RM}		190 200 205		A A A
恢复电荷 Recovered charge	I_F = 200 A, - di_F/dt = 5400 A/µs (T_{vj}=150°C) V_R = 600 V V_{GE} = -15 V	T_{vj} = 25°C T_{vj} = 125°C T_{vj} = 150°C	Q_r		19,5 36,5 42,5		µC µC µC
反向恢复损耗（每脉冲） Reverse recovery energy	I_F = 200 A, - di_F/dt = 5400 A/µs (T_{vj}=150°C) V_R = 600 V V_{GE} = -15 V	T_{vj} = 25°C T_{vj} = 125°C T_{vj} = 150°C	E_{rec}		8,00 14,5 16,5		mJ mJ mJ
结 - 外壳热阻 Thermal resistance, junction to case	每个二极管 / per diode		R_{thJC}			0,203	K/W
外壳 - 散热器热阻 Thermal resistance, case to heatsink	每个二极管 / per diode λ_{Paste} = 1 W/(m·K) / λ_{grease} = 1 W/(m·K)		R_{thCH}		0,133		K/W
在开关状态下温度 Temperature under switching conditions			$T_{vj\,op}$	-40		150	°C

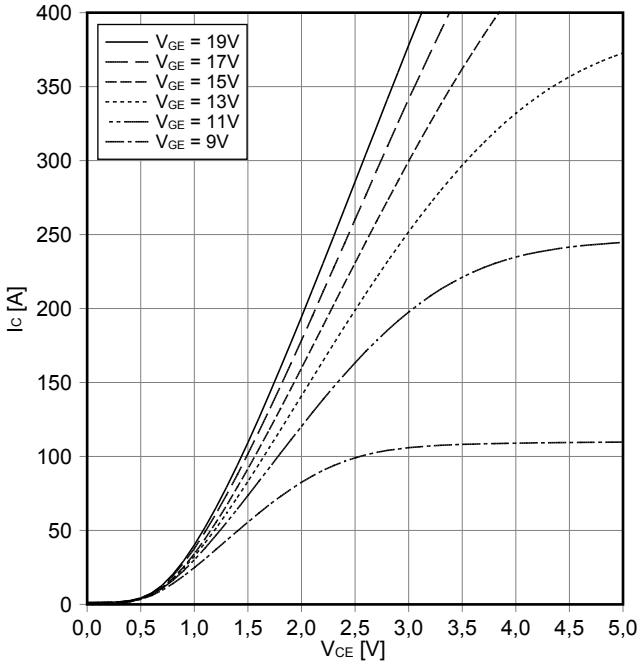
模块 / Module

绝缘测试电压 Isolation test voltage	RMS, f = 50 Hz, t = 1 min.	V_{ISOL}		2,5		kV
模块基板材料 Material of module baseplate				Cu		
内部绝缘 Internal isolation	基本绝缘 (class 1, IEC 61140) basic insulation (class 1, IEC 61140)			Al_2O_3		
爬电距离 Creepage distance	端子至散热器 / terminal to heatsink 端子至端子 / terminal to terminal			29,0 23,0		mm
电气间隙 Clearance	端子至散热器 / terminal to heatsink 端子至端子 / terminal to terminal			23,0 11,0		mm
相对电痕指数 Comperative tracking index		CTI		> 200		
			min.	typ.	max.	
杂散电感,模块 Stray inductance module		L_{sCE}		20		nH
模块引线电阻,端子-芯片 Module lead resistance, terminals - chip	T_C = 25°C, 每个开关 / per switch	$R_{CC'+EE'}$		0,70		mΩ
储存温度 Storage temperature		T_{stg}	-40		125	°C
模块安装的安装扭距 Mounting torque for modul mounting	螺丝 M6 根据相应的应用手册进行安装 Screw M6 - Mounting according to valid application note	M	3,00		6,00	Nm
端子联接扭距 Terminal connection torque	螺丝 M6 根据相应的应用手册进行安装 Screw M6 - Mounting according to valid application note	M	2,5	-	5,0	Nm
重量 Weight		G		285		g

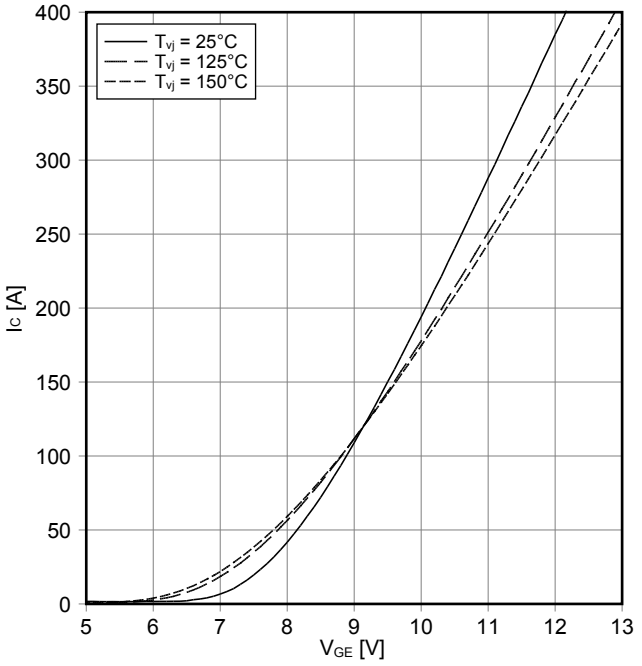
输出特性 IGBT, 逆变器 （典型)
output characteristic IGBT,Inverter (typical)
$I_C = f(V_{CE})$
V_{GE} = 15 V



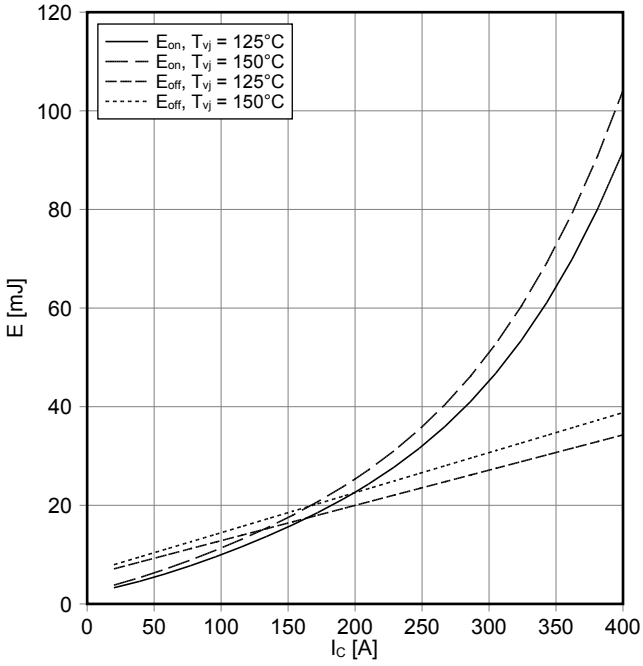
输出特性 IGBT, 逆变器 （典型)
output characteristic IGBT,Inverter (typical)
$I_C = f(V_{CE})$
T_{vj} = 150°C



传输特性 IGBT, 逆变器 (典型)
transfer characteristic IGBT,Inverter (typical)
$I_C = f(V_{GE})$
V_{CE} = 20 V



开关损耗 IGBT, 逆变器 （典型)
switching losses IGBT,Inverter (typical)
$E_{on} = f(I_C)$, $E_{off} = f(I_C)$
V_{GE} = ±15 V, R_{Gon} = 0.62 Ω, R_{Goff} = 0.62 Ω, V_{CE} = 600 V



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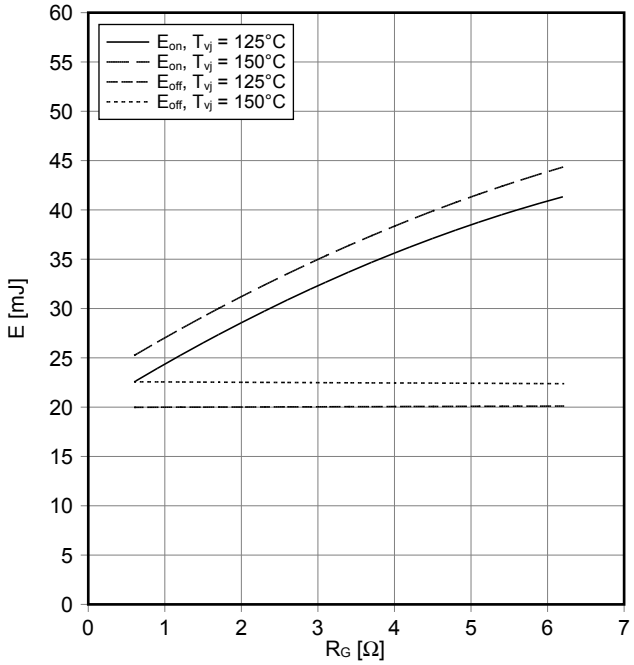
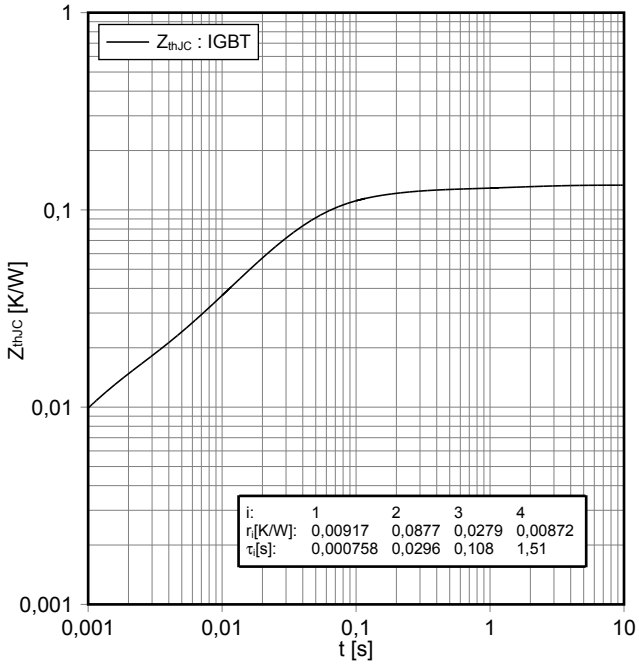
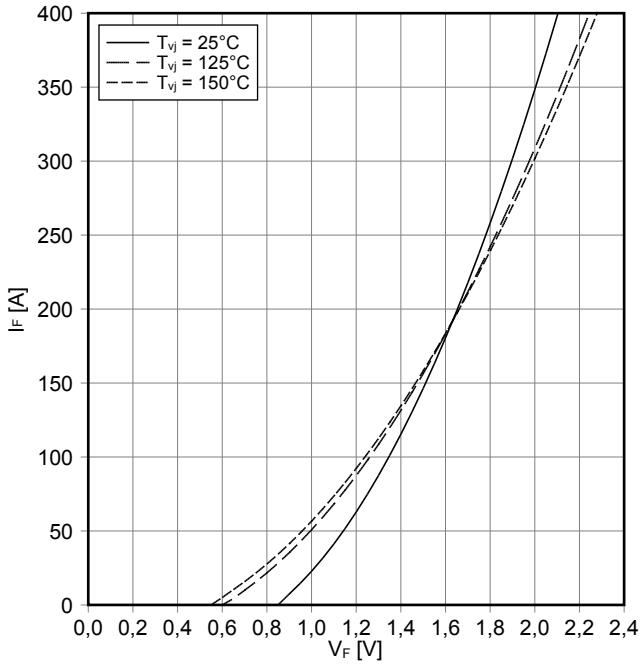
开关损耗 IGBT, 逆变器 （典型)
switching losses IGBT,Inverter (typical)
$E_{on} = f(R_G)$, $E_{off} = f(R_G)$
V_{GE} = ±15 V, I_C = 200 A, V_{CE} = 600 V



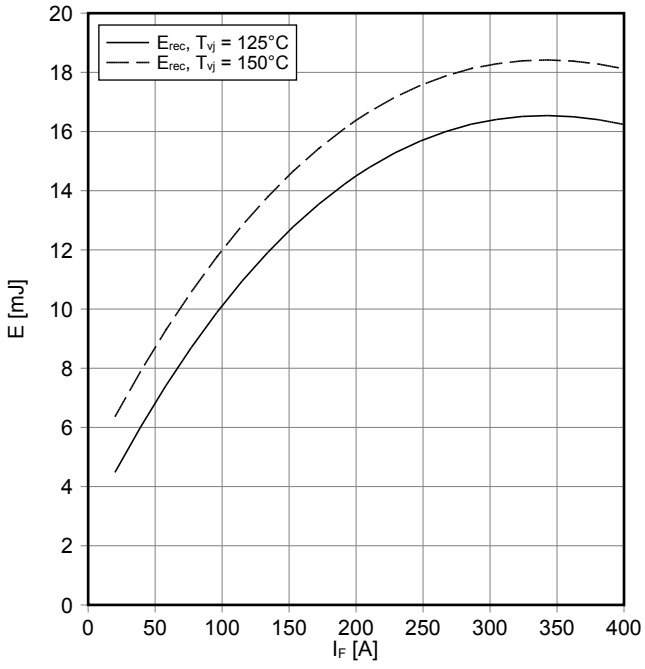
瞬态热阻抗 IGBT, 逆变器
transient thermal impedance IGBT,Inverter
$Z_{thJC} = f(t)$



正向偏压特性 二极管,逆变器 （典型)
forward characteristic of Diode, Inverter (typical)
$I_F = f(V_F)$



开关损耗 二极管,逆变器 （典型)
switching losses Diode, Inverter (typical)
$E_{rec} = f(I_F)$
R_{Gon} = 0.62 Ω, V_{CE} = 600 V



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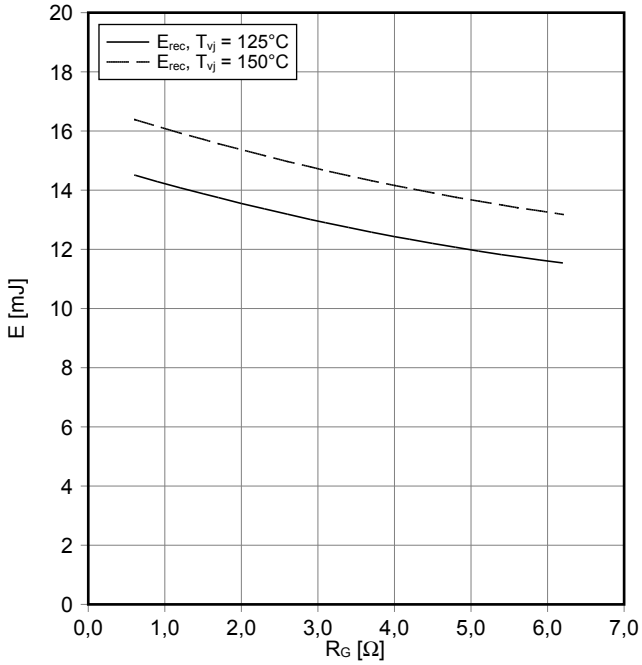
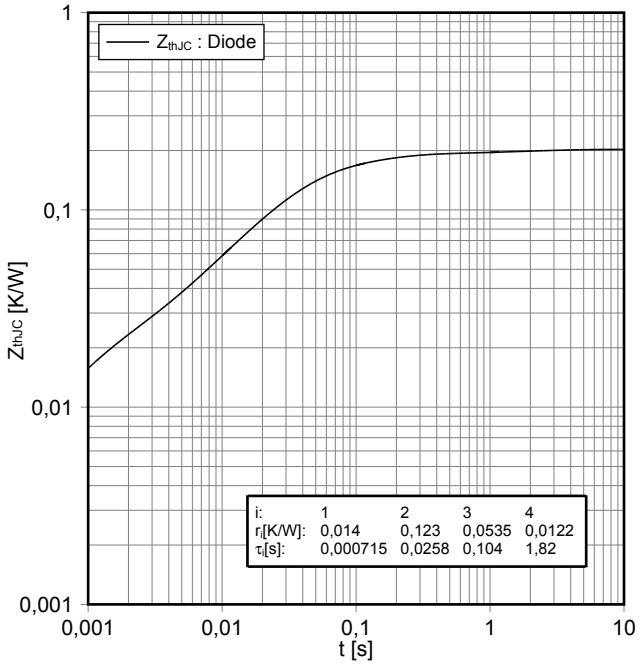
开关损耗 二极管,逆变器 (典型)
switching losses Diode, Inverter (typical)
$E_{rec} = f(R_G)$
$I_F = 200\ A,\ V_{CE} = 600\ V$



瞬态热阻抗 二极管,逆变器
transient thermal impedance Diode, Inverter
$Z_{thJC} = f(t)$



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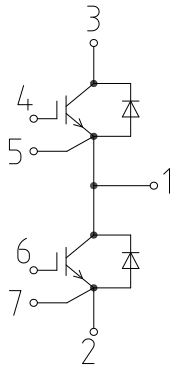
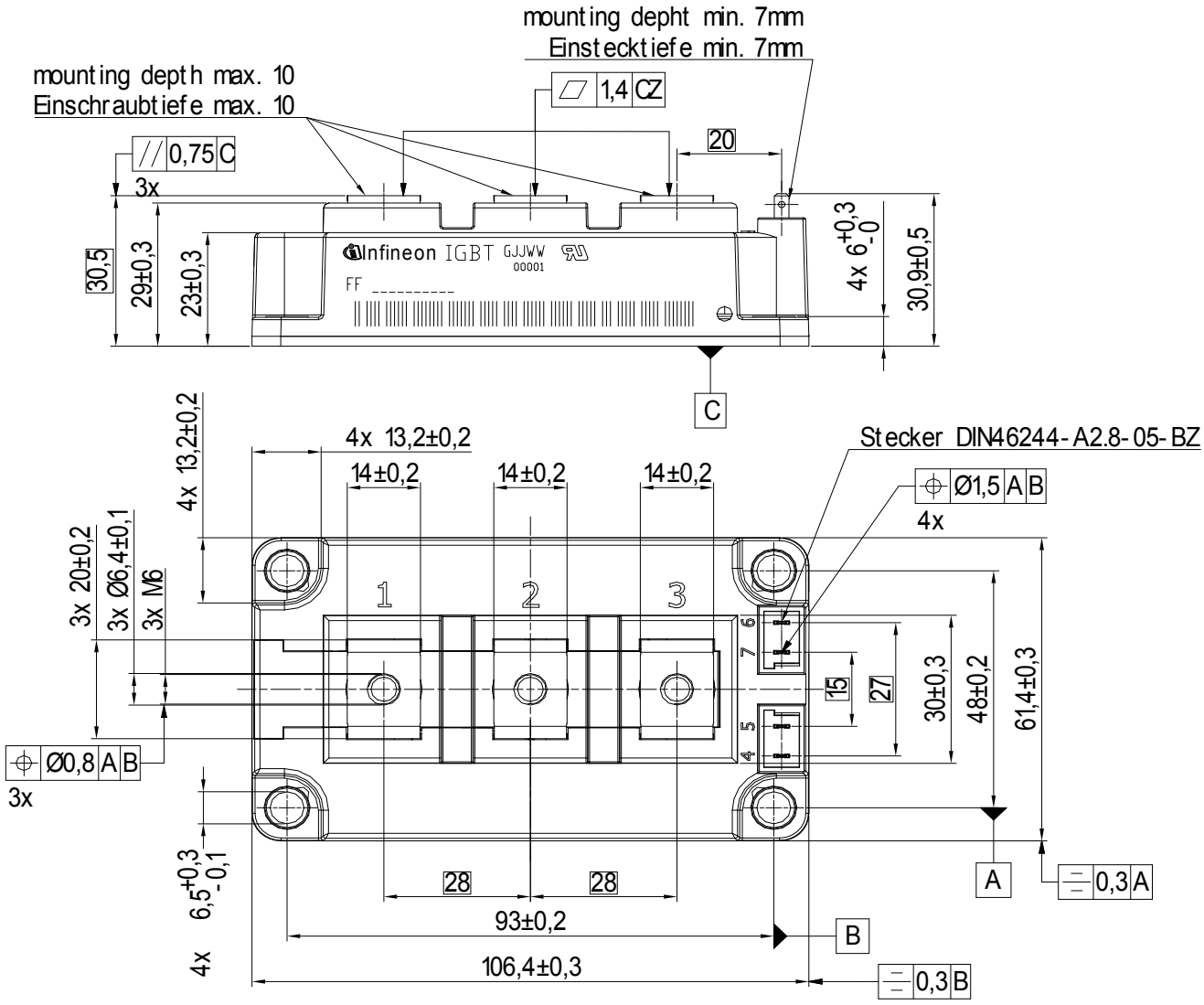
接线图 / Circuit diagram



封装尺寸 / Package outlines



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